

MMG100HB060B6EN

600V 100A IGBT Module

February 2017

Version 2

RoHS Compliant

PRODUCT FEATURES

IGBT³ CHIP(Trench+Field Stop technology)

High short circuit capability,self limiting short circuit cu2(B)-854)tititi.ls4O85o07 TTT4 1 Tf1.47.645.8PTJ81Febrat814Twch+FiBTVCESCollector

APPLICATIONS

GES	Gate Emitter Voltage		$T_j=25$		600VV	
					± 20	
C	DC Collector Current	T	$T_C=25,$	$J_{max}=175$	125	
		T	$C=70,$			A

Unit

mA
mA
nA

μ C
nF
pF
ns
ns
ns
ns
ns
ns
ns

ns

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NTC CHARACTERISTICS ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions	Min.	Typ.	Max.	Unit
R_{25}	Resistance $T_C=25$		5		K K

Unit

V
Nm
Nm
g

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Figure 14. Circuit Diagram